

## Description

The FDS4435BZ uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

### **General Features**

V<sub>DS</sub> =-30V I<sub>D</sub> =-9.5A

 $R_{DS(ON)} < 20m\Omega @ V_{GS}=10V$ 

# Application

Battery protection

Load switch

Uninterruptible power supply

#### Package Marking and Ordering Information

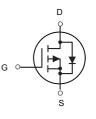
Product ID	Pack	Marking	Qty(PCS)
FDS4435BZ	SOP-8	4435 XXX YYYY	3000

#### Absolute Maximum Ratings (Tc=25°C unless otherwise noted )

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	- 30	V
VGS	Gate-Source Voltage	<u>+</u> 20	V
I₀@T₄=25°C	Drain Current³, V <sub>GS</sub> @ 10V	-9.5	А
I <sub>D</sub> @T <sub>A</sub> =70°C	Drain Current <sup>3</sup> , V <sub>GS</sub> @ 10V	-7.3	А
IDM	Pulsed Drain Current <sup>1</sup>	-50	А
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
Rthj-a	Maximum Thermal Resistance, Junction-ambient <sup>3</sup>	50	°C/W



SOP-8



P-Channel MOSFET



Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-	V
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-7A	-	18	20	mΩ
RDS(ON)	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-5A	-	32	36	mΩ
VGS(th)	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-1	-	-3	V
<b>g</b> fs	Forward Transconductance	V <sub>DS</sub> =-10V, I <sub>D</sub> =-7A	-	16	-	S
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V	-	-	-30	uA
IGSS	Gate-Source Leakage	V <sub>GS</sub> = <u>+</u> 20V, V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Qg	Total Gate Charge	I <sub>D</sub> =-7A	-	18	29	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-24V	-	3	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =-4.5V	-	10	-	nC
td(on)	Turn-on Delay Time	V <sub>DS</sub> =-15V	-	8	-	ns
tr	Rise Time	I <sub>D</sub> =-1A	-	6.6	-	ns
td(off)	Turn-off Delay Time	R <sub>G</sub> =3.3Ω	-	44	-	ns
tr	Fall Time	V <sub>GS</sub> =-10V	-	34	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	1175	1690	pF
Coss	Output Capacitance	V <sub>DS</sub> =- 25V	-	195	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	190	-	pF
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =-2.1A, V <sub>GS</sub> =0V	-	-	-1.2	V
trr	Reverse Recovery Time	Is=-7A, V <sub>GS</sub> =0V, dl/dt=100A/µs	-	28	-	ns
Qrr	Reverse Recovery Charge		-	18	-	nC

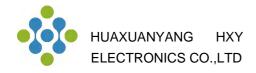
# Electrical Characteristics@Tj=25°C(unless otherwise specified)

# Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board, t  $\leq$ 10sec ; 125 °C/W when mounted on Min. cop



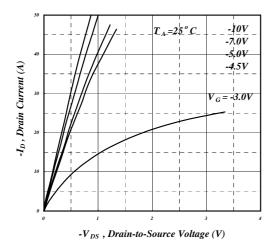


Fig 1. Typical Output Characteristics

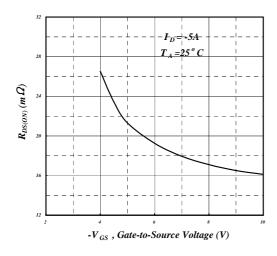
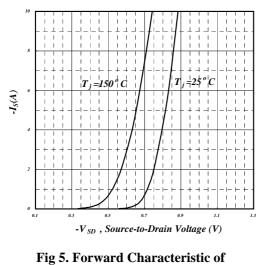


Fig 3. On-Resistance v.s. Gate Voltage



Reverse Diode

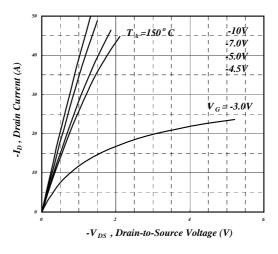


Fig 2. Typical Output Characteristics

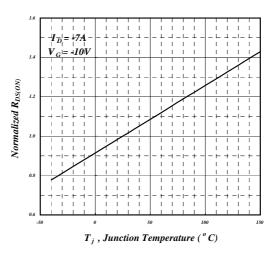


Fig 4. Normalized On-Resistance v.s. Junction Temperature

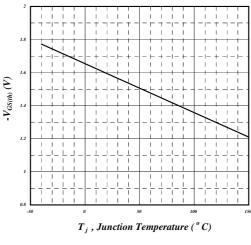
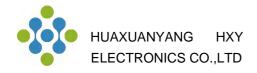


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



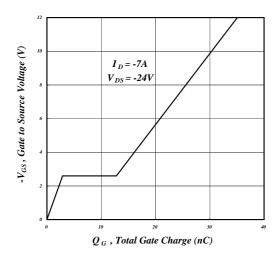


Fig 7. Gate Charge Characteristics

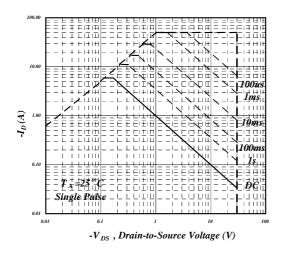


Fig 9. Maximum Safe Operating Area

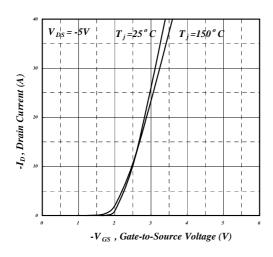


Fig 11. Transfer Characteristics

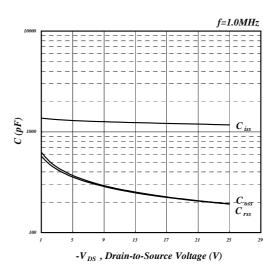


Fig 8. Typical Capacitance Characteristics

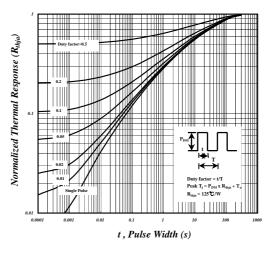


Fig 10. Effective Transient Thermal Impedance

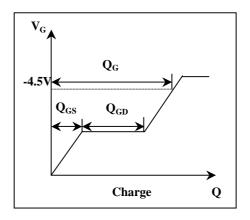
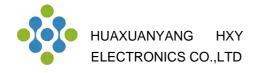
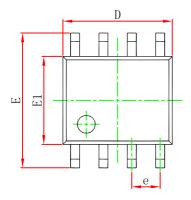
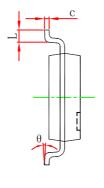


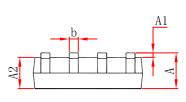
Fig 12. Gate Charge Circuit



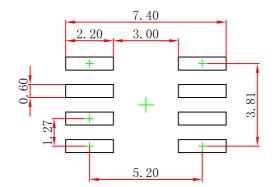
# SOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
с	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0.197	
e	1.270 (BSC)		0.050 (BSC)		
E	5.800	6.200	0.228	0.244	
E1	3.800	4.000	0.150	0.157	
L	0.400	1.270	0.016	0.050	
θ	0 °	8°	0 °	8°	



- Note: 1.Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
   3.The pad layout is for reference purposes only.



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